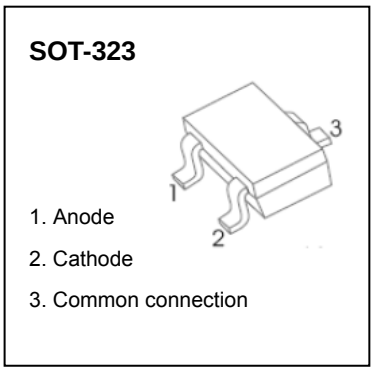
General purpose PIN diode



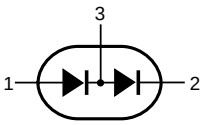


Fig.1 Simplified outline (SOT323) and symbol.

FEATURES

- Two elements in series configuration in a small SMD plastic package
- Low diode capacitance
- Low diode forward resistance.

APPLICATIONS

- General RF applications.

DESCRIPTION

Two planar PIN diodes in series configuration in an SOT323 small SMD plastic package.

Marking code: 6W

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per diode					
V_R	continuous reverse voltage		–	50	V
I_F	continuous forward current		–	50	mA
P_{tot}	total power dissipation	T_s = 90 °C	–	240	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–65	+150	°C

ELECTRICAL CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
Per diode						
V_F	forward voltage	I_F = 50 mA	–	0.95	1.1	V
V_R	reverse voltage	I_R = 10 µA	50	–	–	V
I_R	reverse current	V_R = 50 V	–	–	100	nA
C_d	diode capacitance	V_R = 0; f = 1 MHz	–	0.45	–	pF
		V_R = 1 V; f = 1 MHz	–	0.35	0.6	pF
		V_R = 5 V; f = 1 MHz	–	0.30	0.5	pF
r_D	diode forward resistance	I_F = 0.5 mA; f = 100 MHz; note 1	–	25	40	Ω
		I_F = 1 mA; f = 100 MHz; note 1	–	14	25	Ω
		I_F = 10 mA; f = 100 MHz; note 1	–	3	5	Ω
τ_L	charge carrier life time	when switched from I_F = 10 mA to I_R = 6 mA; R_L = 100 Ω; measured at I_R = 3 mA	–	1.05	–	µs
L_S	series inductance	I_F = 10 mA; f = 100 MHz	–	1.60	–	nH

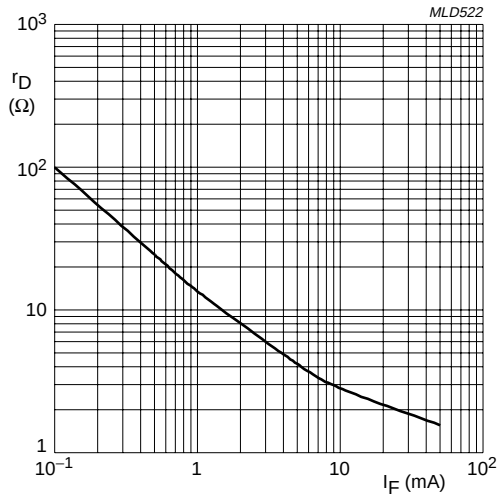
Note

1. Guaranteed on AQL basis: inspection level S4, AQL 1.0.

THERMAL CHARACTERISTICS

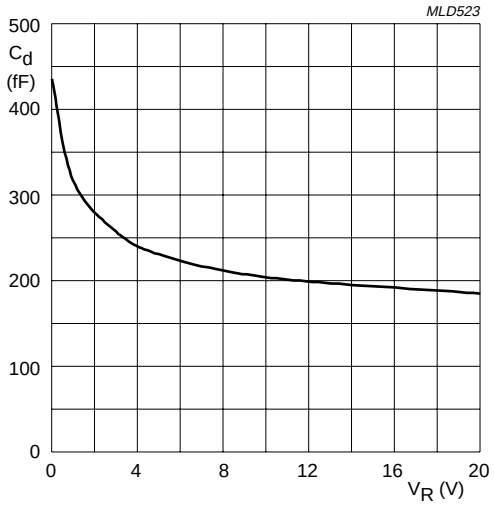
SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j\text{-}s}$	thermal resistance from junction to soldering point	250	K/W

GRAPHICAL DATA



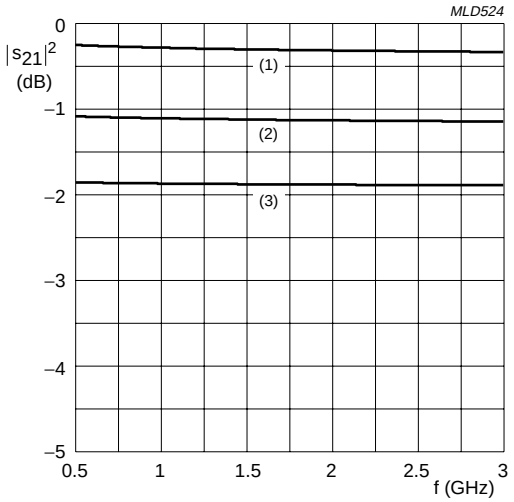
f = 100 MHz; T_j = 25 °C.

Fig.2 Forward resistance as a function of forward current; typical values.



f = 1 MHz; T_j = 25 °C.

Fig.3 Diode capacitance as a function of reverse voltage; typical values.

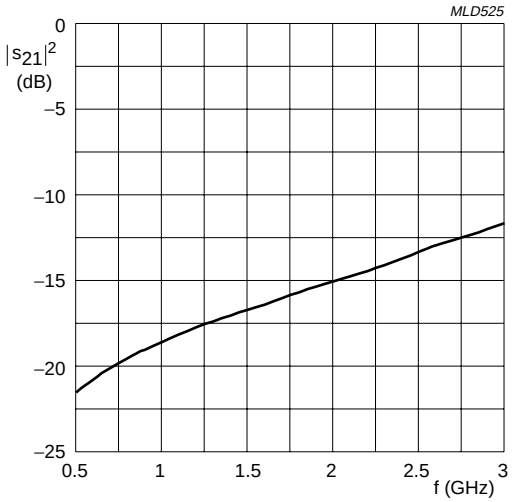


(1) I_F = 10 mA. (2) I_F = 1 mA. (3) I_F = 0.5 mA.

Diode inserted in series with a 50 Ω stripline circuit and biased via the analyzer Tee network.

T_{amb} = 25 °C.

Fig.4 Insertion loss ($|s_{21}|^2$) of the diode in on-state as a function of frequency; typical values.



Diode zero biased and inserted in series with a 50 Ω stripline circuit.

T_{amb} = 25 °C.

Fig.5 Isolation ($|s_{21}|^2$) of the diode in off-state as a function of frequency; typical values.